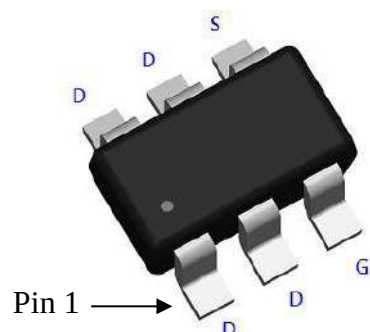


N-Channel Enhancement Mode MOSFET

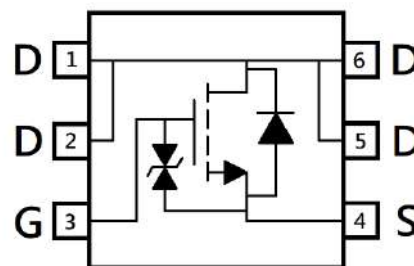
Features:

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic
- ESD protected gate

SOT-26



BV_{DSS}	100V
$I_D @ V_{GS}=10V, T_C=25^\circ C$	3.2A
$I_D @ V_{GS}=10V, T_A=25^\circ C$	2.6A
$R_{DS(ON)} \text{ typ. } @ V_{GS}=10V, I_D=2A$	105m Ω
$R_{DS(ON)} \text{ typ. } @ V_{GS}=4.5V, I_D=2A$	160m Ω



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KWB100N10RK	SOT-26 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Absolute Maximum Ratings (T_A=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @ V _{GS} =10V, T _C =25°C	I _D	3.2	A
Continuous Drain Current @ V _{GS} =10V, T _C =100°C		2	
Continuous Drain Current @ V _{GS} =10V, T _A =25°C		2.6	
Continuous Drain Current @ V _{GS} =10V, T _A =70°C		2	
Pulsed Drain Current	I _{DM}	12	
Continuous Body Diode Forward Current @ T _C =25°C	I _S	2.5	W
Total Power Dissipation	P _D	3.1	
		1.2	
		2	
		1.3	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Steady State	Unit
Thermal Resistance, Junction-to-case	R _{θJC}	40	°C/W
Thermal Resistance, Junction-to-ambient	R _{θJA}	62.5	

Note:

- *a. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- *b. The value of R_{θJA} is measured with the device mounted on 1 in² FR -4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_D is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- *c. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	100	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1	-	2.5		V _{DS} =V _{GS} , I _D =250μA
G _{FS}	-	3.2	-	S	V _{DS} =10V, I _D =1A
I _{GSS}	-	-	±10	μA	V _{GS} =±16V, V _{DS} =0V
I _{DSS}	-	-	1		V _{DS} =80V, V _{GS} =0V
R _{DS(ON)}	-	105	135	mΩ	V _{GS} =10V, I _D =2A
	-	160	220		V _{GS} =4.5V, I _D =2A
Dynamic					
C _{iss}	-	250	-	pF	V _{DS} =50V, V _{GS} =0V, f=1MHz
C _{oss}	-	32	-		
C _{rss}	-	16	-		
R _g	-	5.4	-	Ω	f=1MHz
Q _g *1, 2	-	4.2	-	nC	V _{DS} =50V, I _D =2A, V _{GS} =10V
Q _{gs} *1, 2	-	0.7	-		
Q _{gd} *1, 2	-	0.6	-		
t _{d(ON)} *1, 2	-	4.2	-	ns	V _{DS} =50V, I _D =2A, V _{GS} =10V, R _{GS} =1Ω
t _r *1, 2	-	14	-		
t _{d(OFF)} *1, 2	-	12	-		
t _f *1, 2	-	5	-		
Source-Drain Diode					
V _{SD} *1	-	0.84	1.2	V	I _S =2A, V _{GS} =0V
t _{rr}	-	22	-	ns	I _F =2A, dI _F /dt=100A/μs
Q _{rr}	-	21	-	nC	

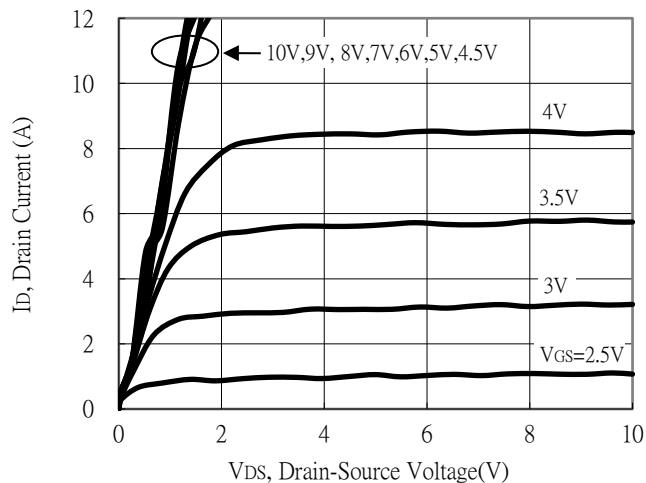
Note:

*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

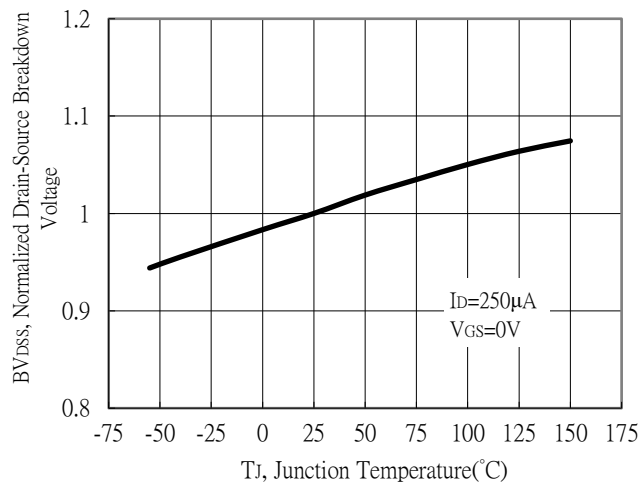
*2. Independent of operating temperature

Typical Characteristics

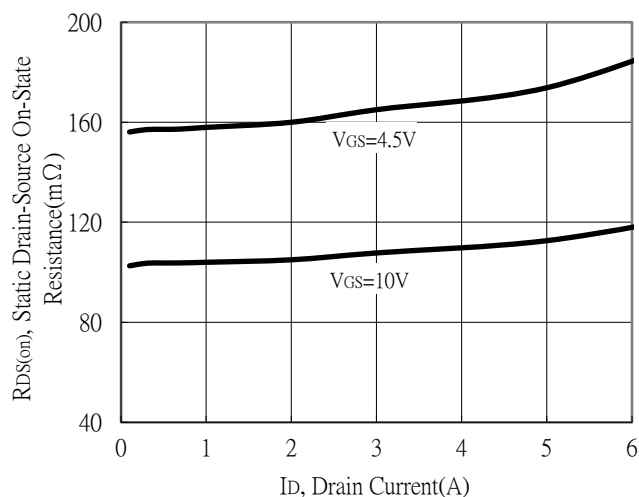
Typical Output Characteristics



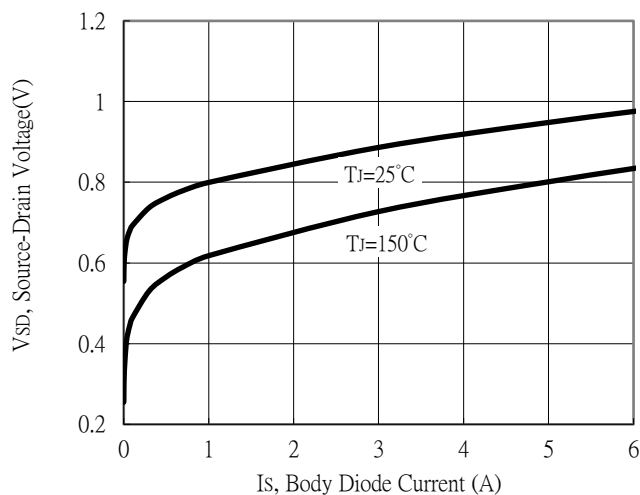
Breakdown Voltage vs Ambient Temperature



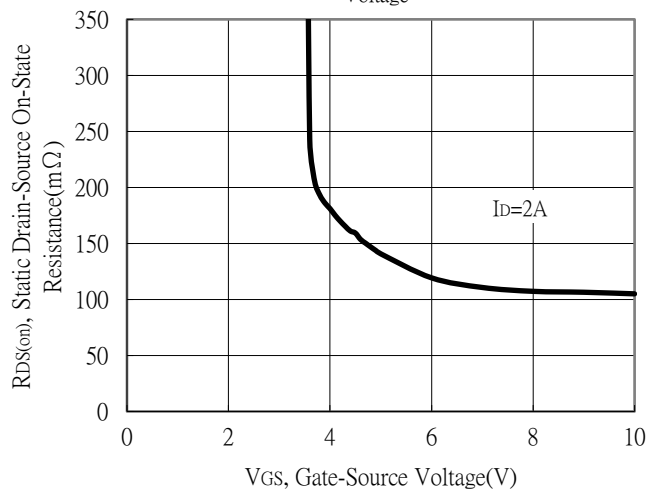
Static Drain-Source On-State resistance vs Drain Current



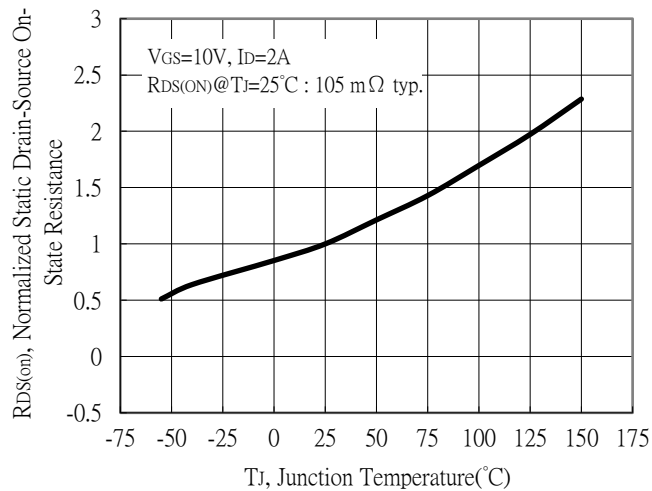
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

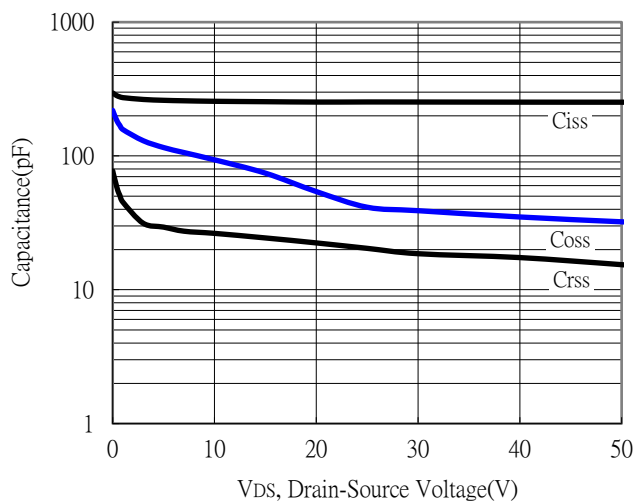


Drain-Source On-State Resistance vs Junction Temperature

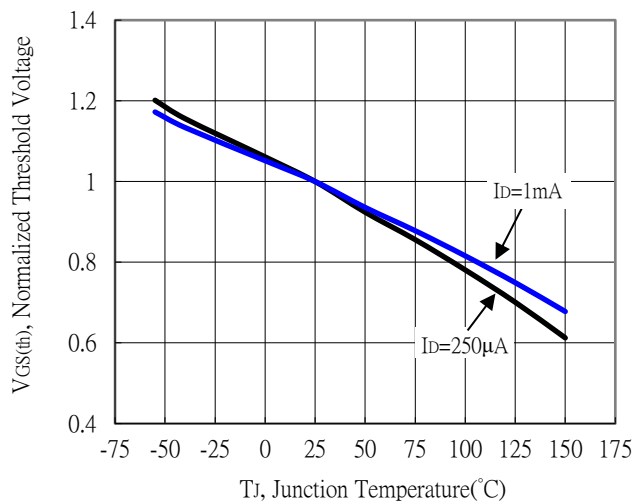


Typical Characteristics (Cont.)

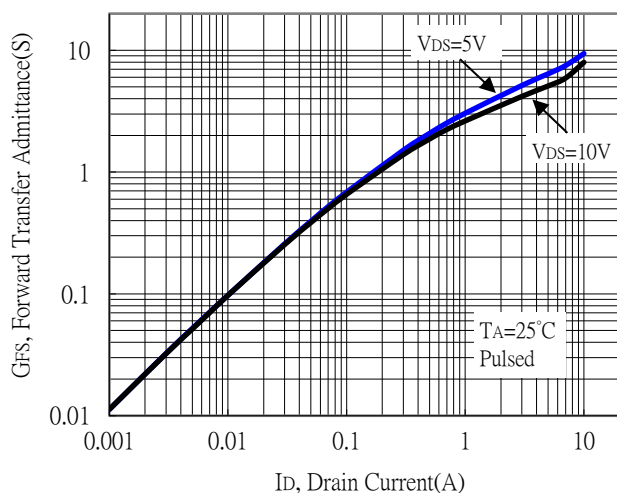
Capacitance vs Drain-to-Source Voltage



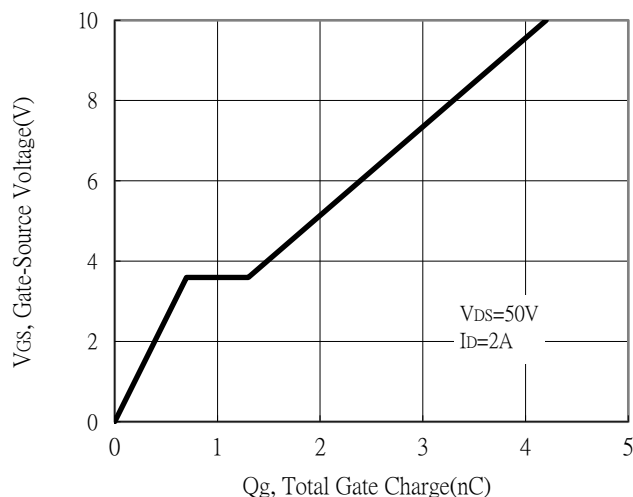
Threshold Voltage vs Junction Temperature



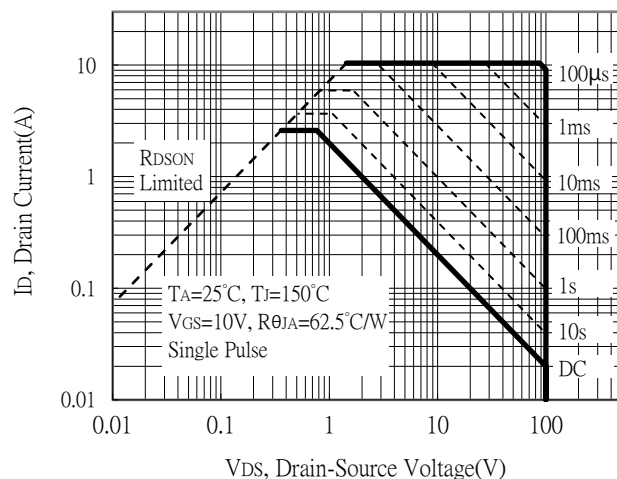
Forward Transfer Admittance vs Drain Current



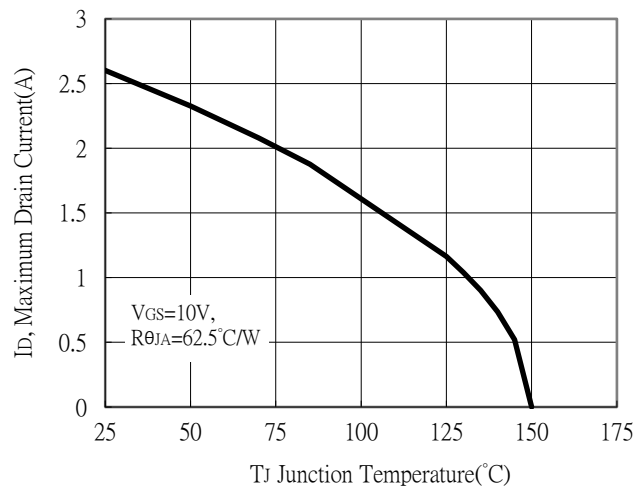
Gate Charge Characteristics



Maximum Safe Operating Area

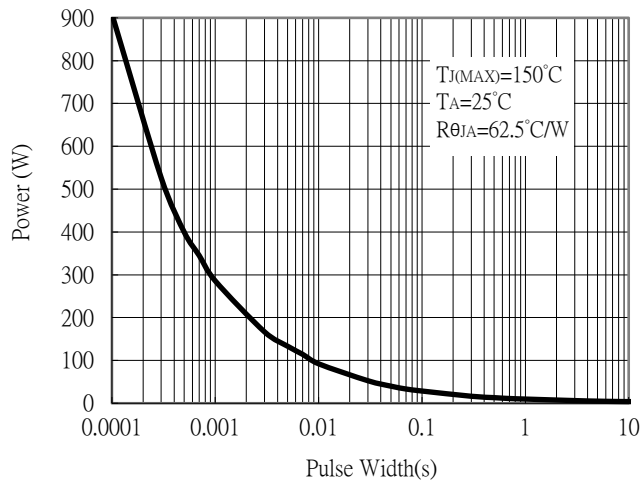


Maximum Drain Current vs Junction Temperature

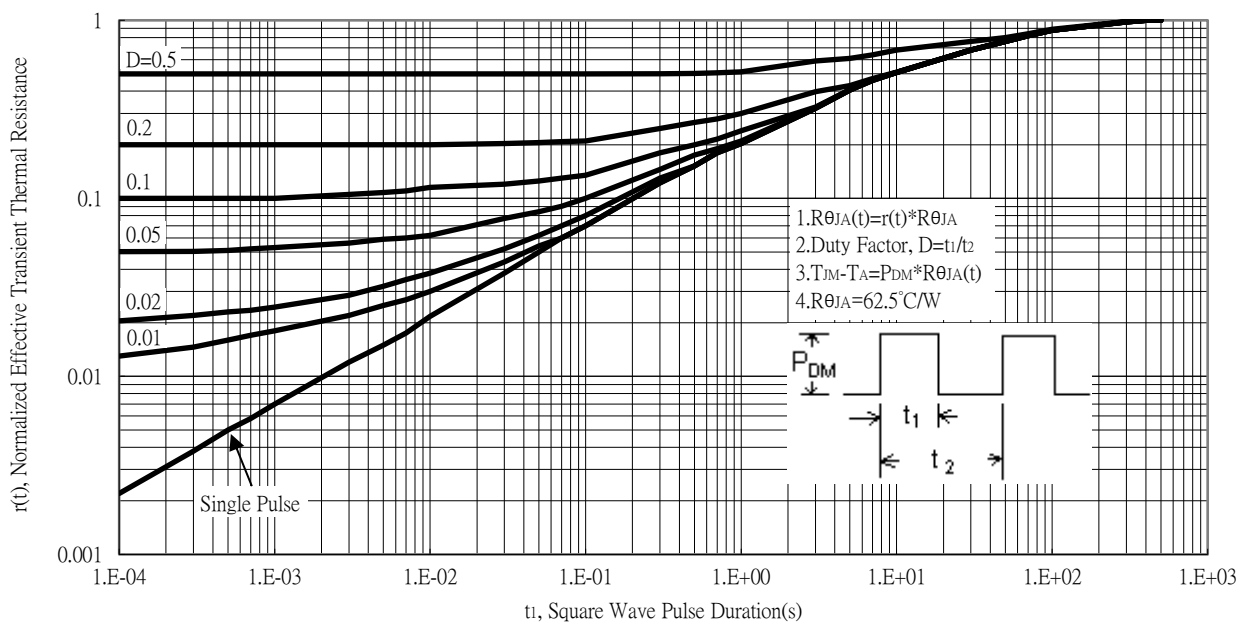


Typical Characteristics (Cont.)

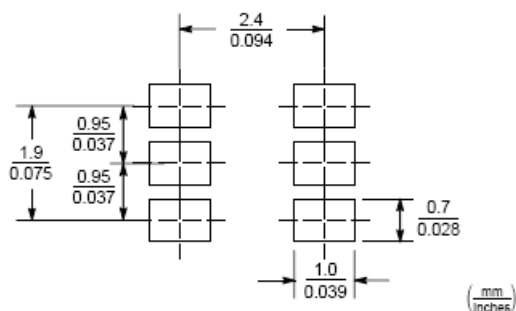
Single Pulse Power Rating, Junction to Ambient



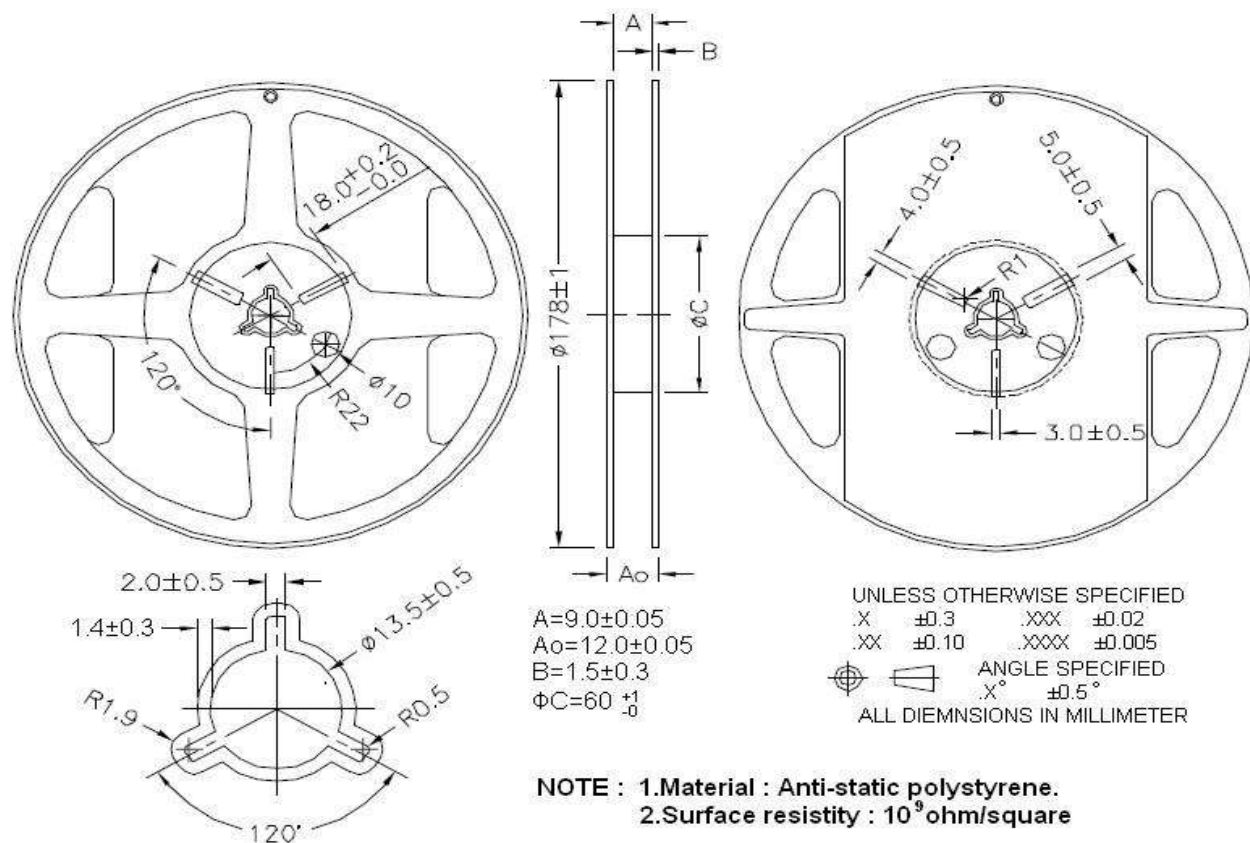
Transient Thermal Response Curves



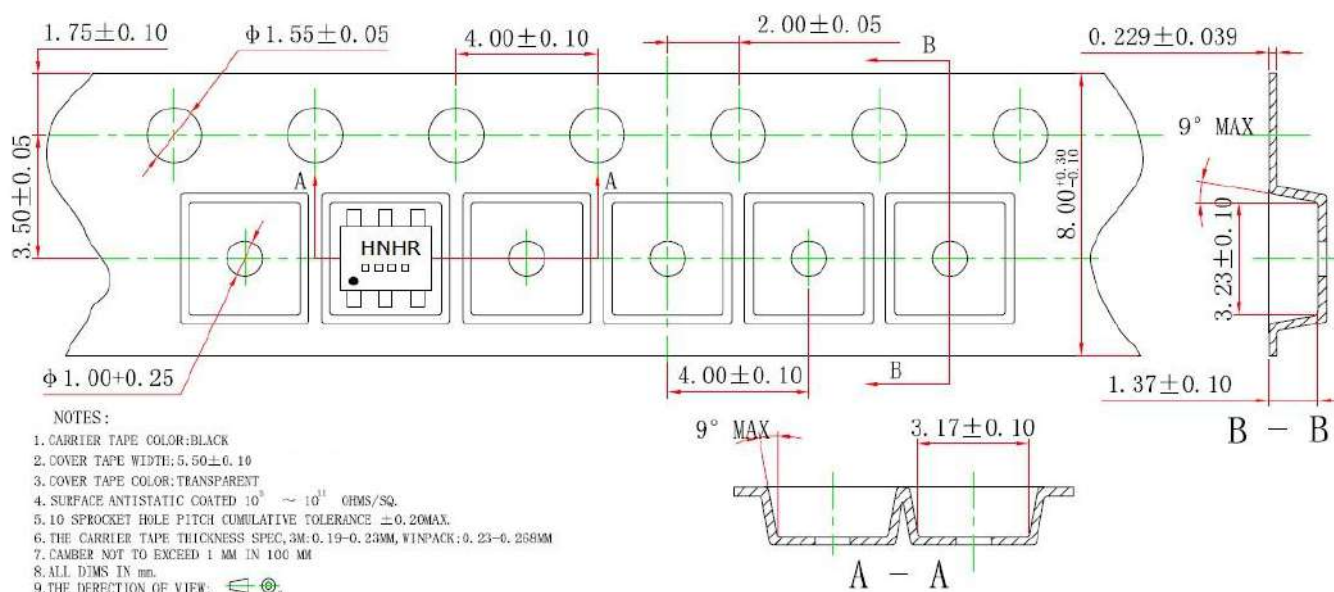
Recommended Soldering Footprint



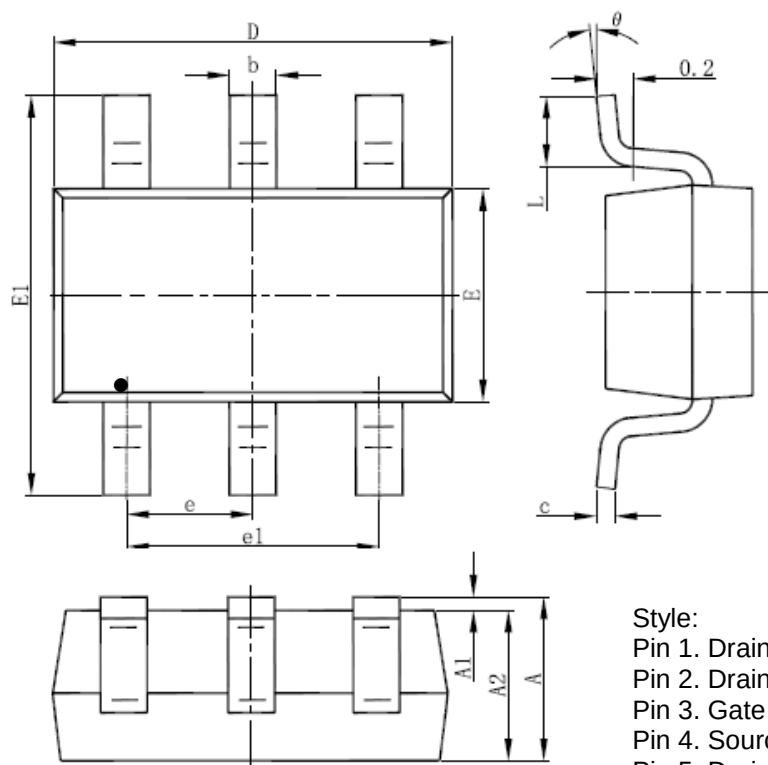
Reel Dimension



Carrier Tape Dimension



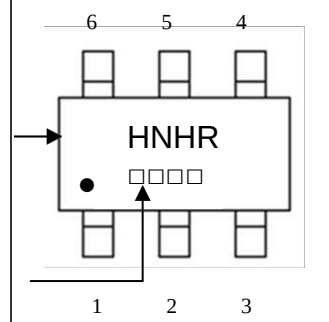
SOT-26 Dimension



Device Name

Date Code

Marking:



6-Lead SOT-26 Plastic
Surface Mounted Package

Style:

Pin 1. Drain (D)
 Pin 2. Drain (D)
 Pin 3. Gate (G)
 Pin 4. Source (S)
 Pin 5. Drain (D)
 Pin 6. Drain (D)

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049	E	1.500	1.700	0.059	0.067
A1	0.000	0.100	0.000	0.004	E1	2.650	2.950	0.104	0.116
A2	1.050	1.150	0.041	0.045	e	0.950	(BSC)	0.037	(BSC)
b	0.300	0.500	0.012	0.020	e1	1.800	2.000	0.071	0.079
c	0.100	0.200	0.004	0.008	L	0.300	0.600	0.012	0.024
D	2.820	3.020	0.111	0.119	θ	0°	8°	0°	8°